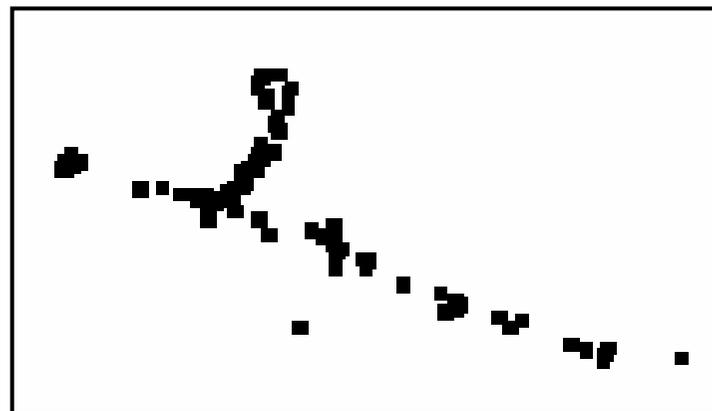


Silicon pixel readout for a TPC

Jan Timmermans - NIKHEF

- Reminder GridPix
- TimePix news
- First & new results InGrid
- First results on protection
- Future developments

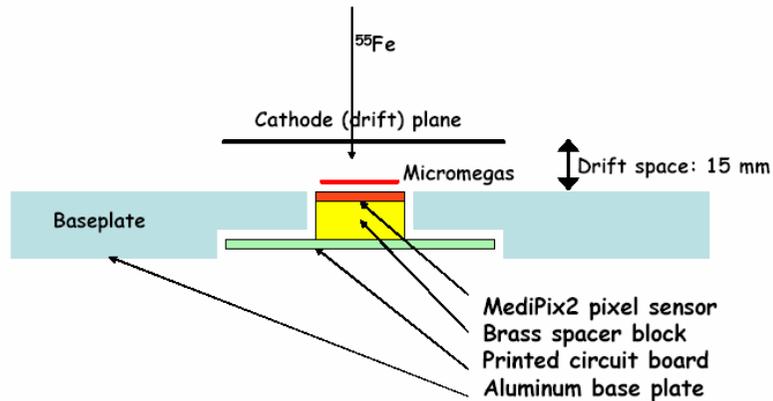


Goals

- **Gas multiplication** GEM or Micromegas foil(s)
- Charge collection with **granularity matching primary ionisation cluster spread**
- Needs **sufficiently low diffusion gas**
- dE/dx using **cluster counting?**
(→ M. Hauschild @ ECFA LC workshop Vienna)
- Proof of principle based on existing **Medipix2** readout chip: **achieved**
- Add 3rd coordinate: **Medipix2** → **TimePix** (→2006)
- Integrate grid with pixel chip: **Ingrid** (new results)

Results pixel readout gas detectors

NIKHEF-Saclay-CERN-Twente



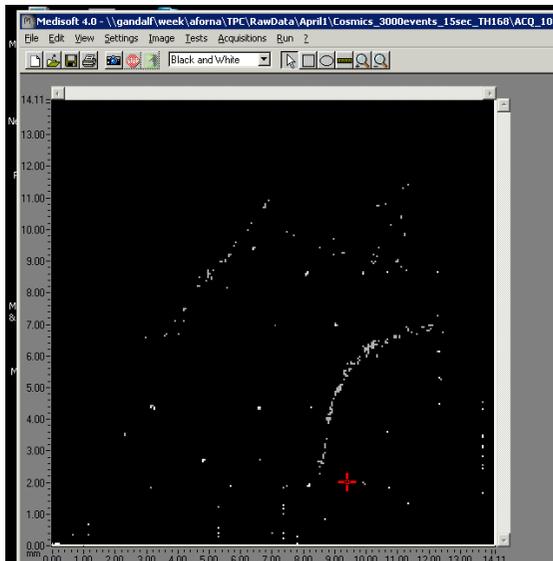
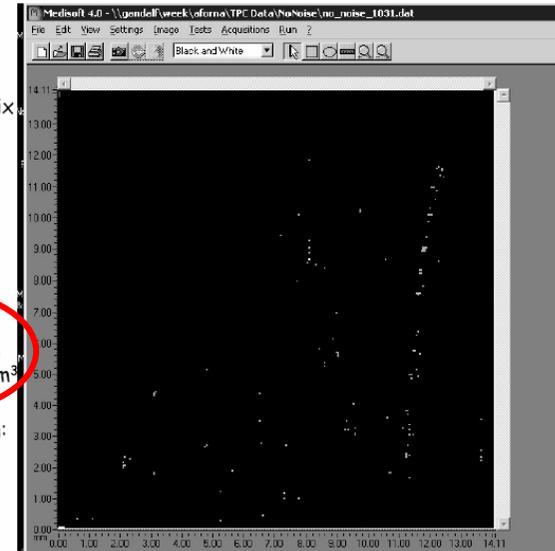
Very strong E-field above (CMOS) MediPix!

He/Isobutane
80/20
Modified MediPix

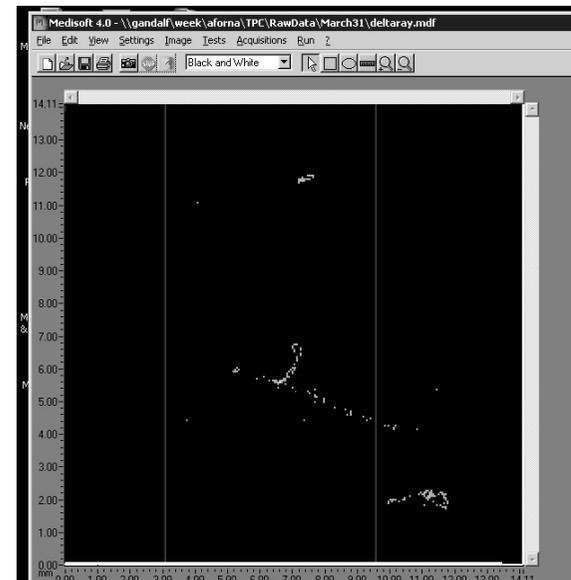
31 March 2004

Sensitive area:
14 x 14 x 15 mm³

Drift direction:
Vertical
max = 15 mm



55x55 μm^2
pixels



δ ray

Observation of min. ionising cosmic muons: high spatial resolution +

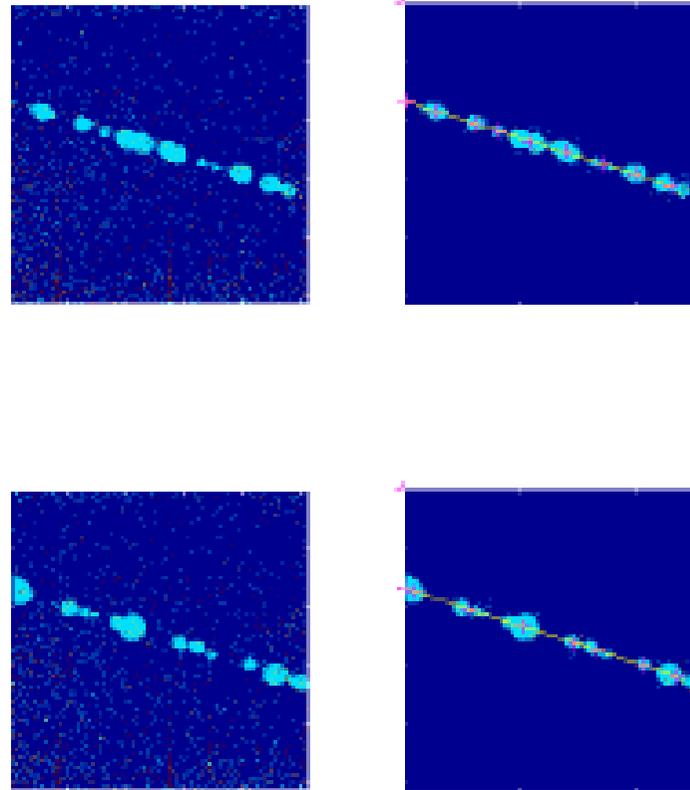
NIM A540 (2005) 295 (physics/0409048)

individual cluster counting !



Some events with fits

(from Freiburg GEM+Medipix setup - Andreas Bamberger)



Difference between Micromegas and GEM setup understood (simulation Michael Hauschild)



Results for point/cluster resolution

(from Freiburg GEM+Medipix setup)

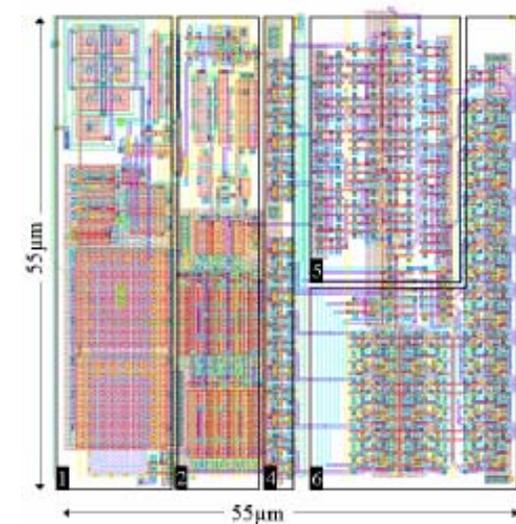
	Ar/CO ₂	He/CO ₂
3-point method	58 ± 2 μm	53 ± 3 μm
$\sigma_{\text{corrected}}^*$	54 μm	53 μm

- **with few primary electrons per cluster !**
- * multiple scattering correction to be checked for systematics

TimePix1 (EUDET: Freiburg, Saclay, CERN, NIKHEF)



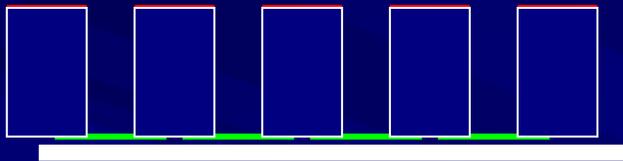
- Distribute clock to full 256x256 pixel matrix (50-100-160MHz)
- Enable counting by first hit after 'shutter' opens, until 'shutter' closes (common stop); also time-over-threshold possible
- Dynamic range $2^{14} \times 10 \text{ ns} = 160 \mu\text{s}$
- (for the time being) no zero-suppress to remain fully compatible with Medipix2
- Shaping time $\sim 200 \text{ ns}$
- Extra static discharge protection for the could be considered later
- Keep same chip-size, pixel-size, readout protocol
- 1st full reticle submit done July 2006



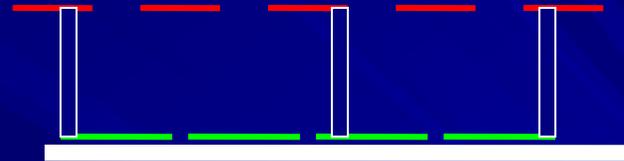
InGrid

Integrate GEM/Micromegas and pixel sensor

'GEM'

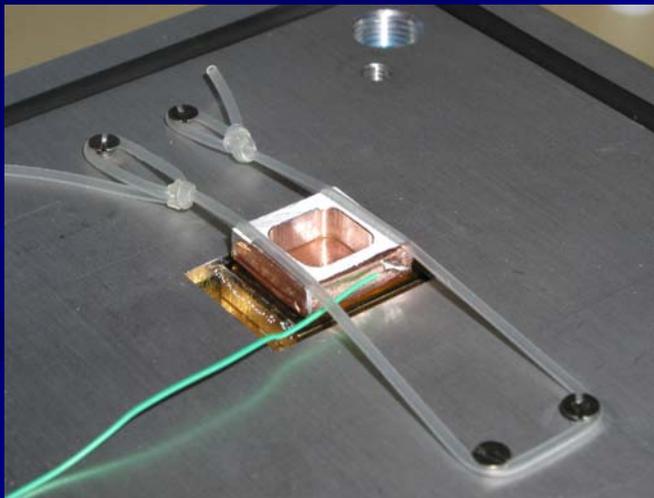


'Micromegas'



By 'wafer post processing'

4" wafer



July 20, 2006

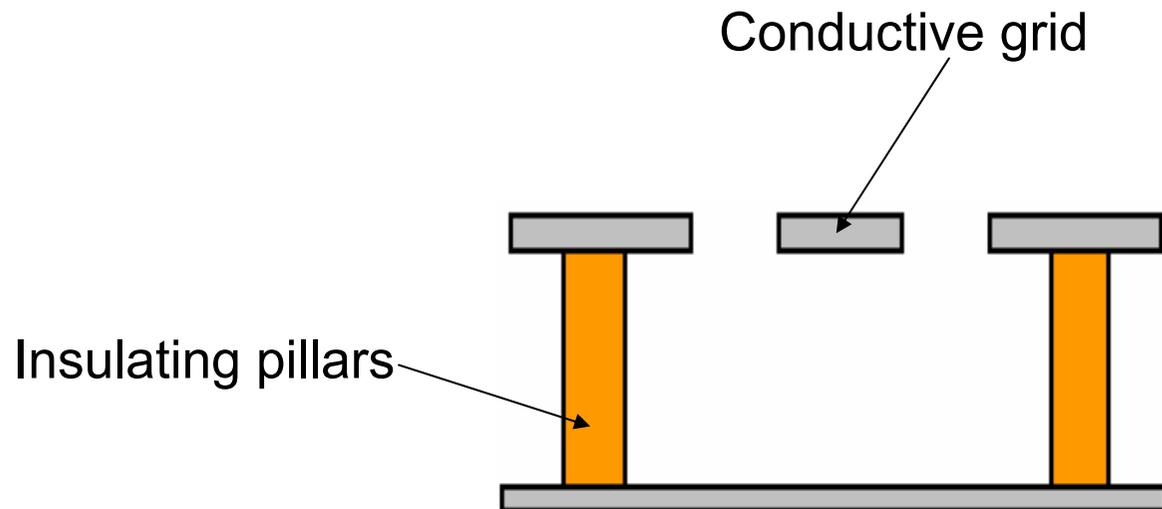
Vancouver L

19 different fields of 15 mm Ø
2 bonding pads / fields

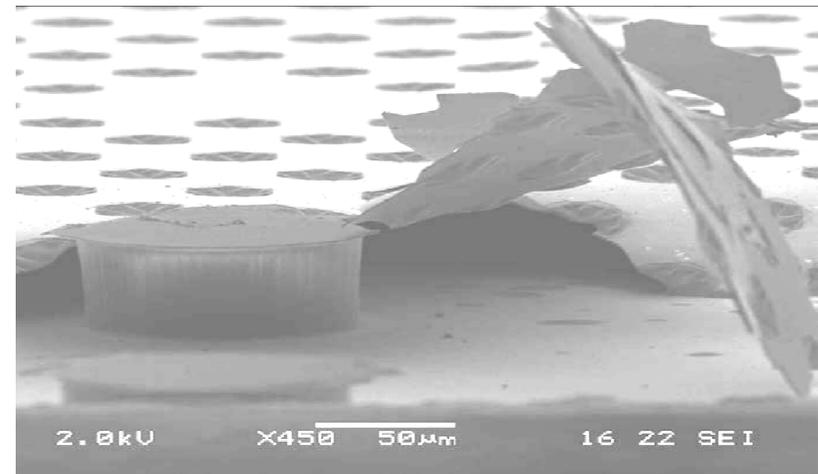
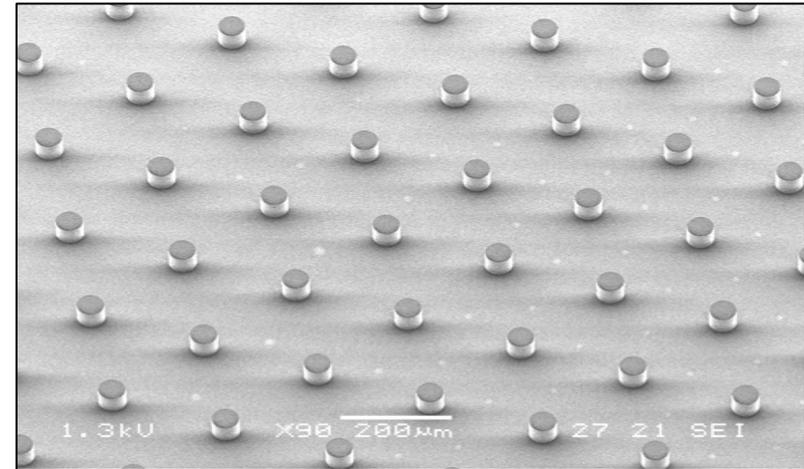
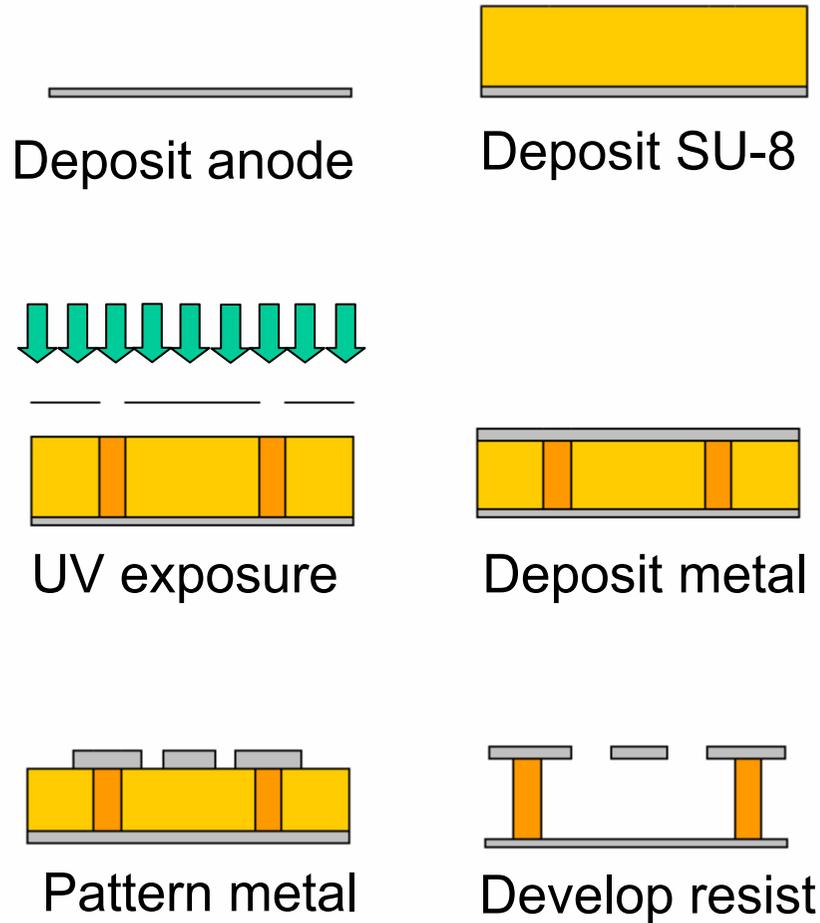
7

Materials for our structures

- SU-8 negative resist as insulating pillars
 - Easy to define structures
 - Wide range of thickness (5 μm to 250 μm)
 - High precision
- Aluminum as conductive grid
 - Commonly used in microelectronics
 - Easy to deposit
 - Easy to pattern

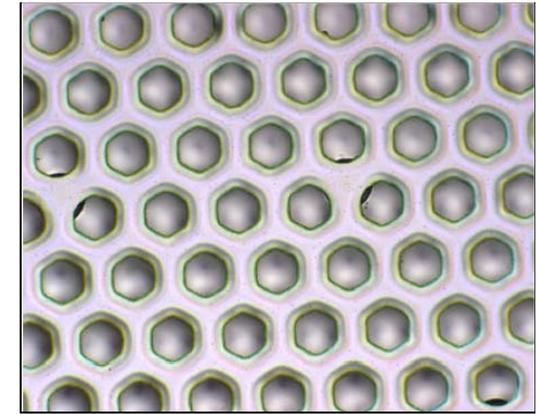


InGrid: Integrated Grid



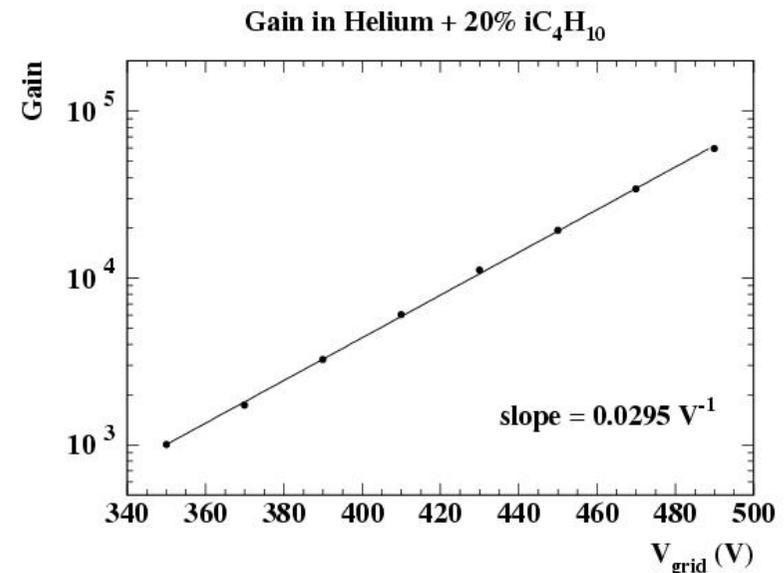
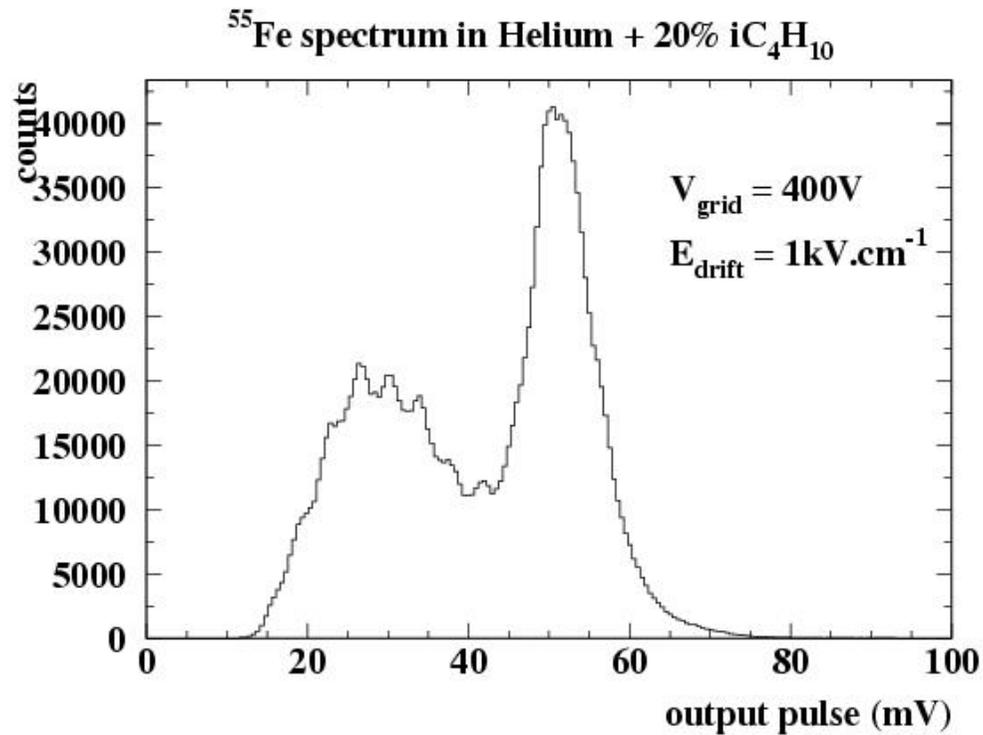
Measuring the InGrid signals

(NIM A556 (2006) 490)



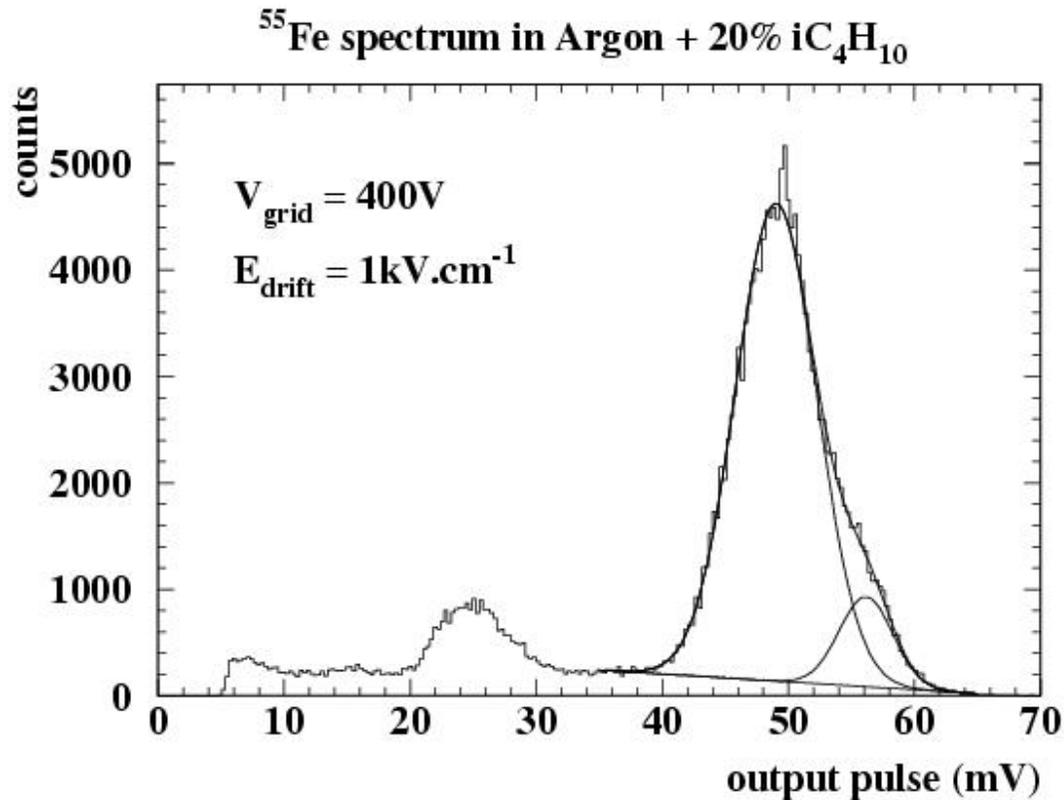
(After 9 months of process tuning and unsuccessful trials)

Pulseheight and gain: He + 20% iC₄H₁₀



•Gas gains $10^3 - 6\cdot 10^4$

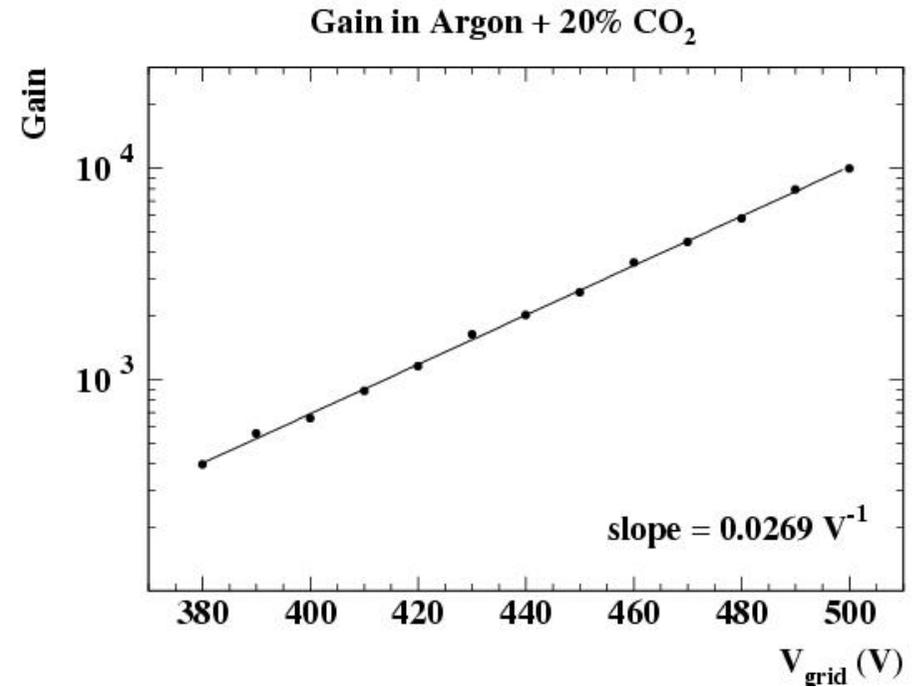
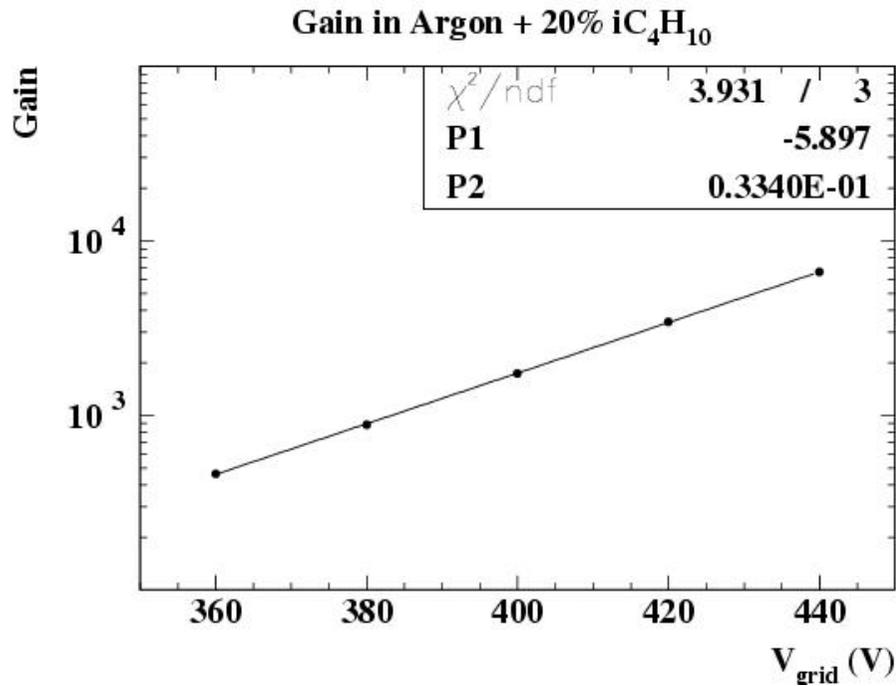
Energy resolution in Argon IsoC4H10 80/20



- Observation of two lines:
 - K_{α} at 5.9 keV
 - K_{β} at 6.4 keV
- Resolution $\sigma_E/E = 6.5\%$
(FWHM = 15.3%)
- Gain variations $< \pm 5\%$

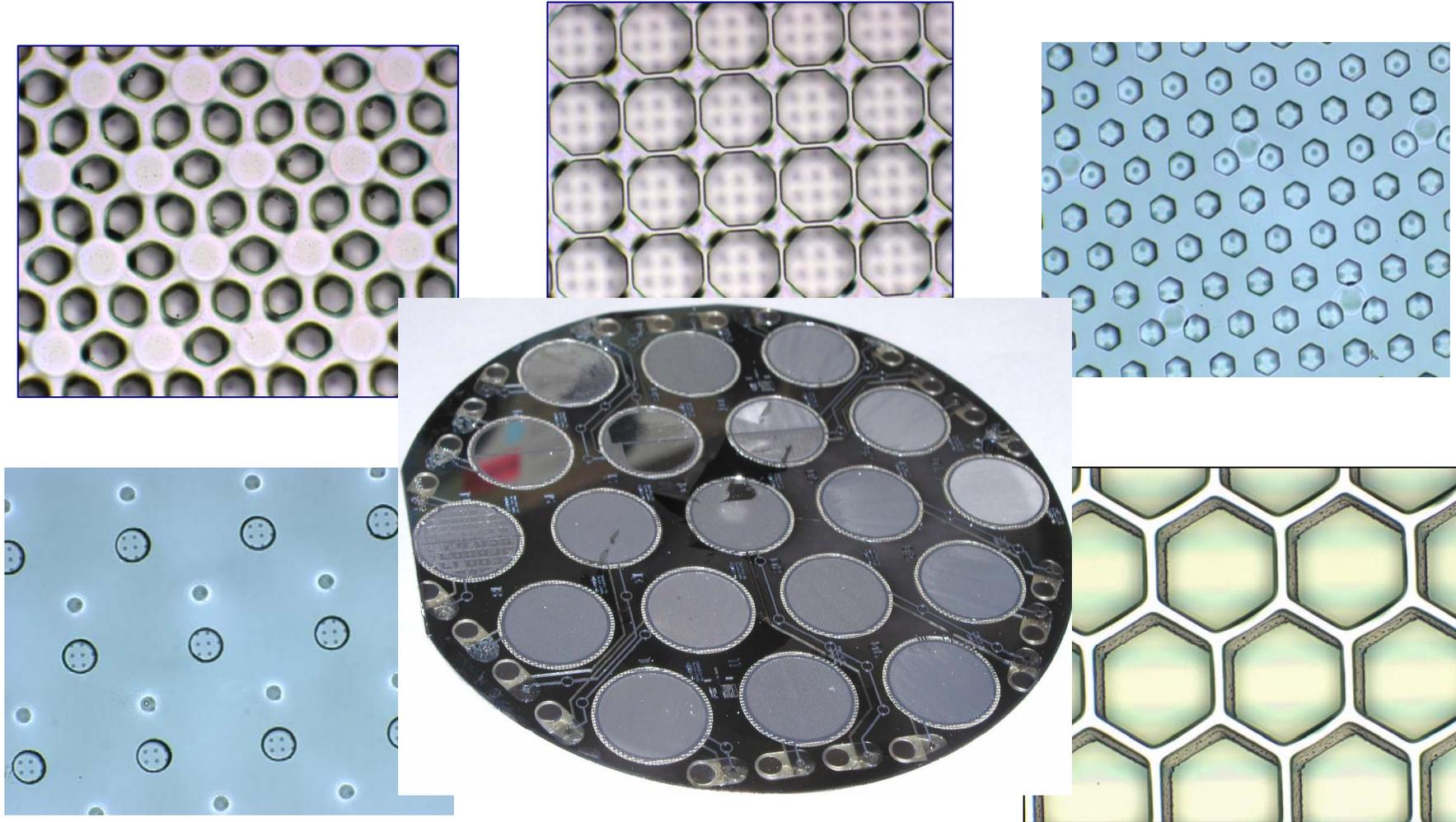
- Photo peak asymmetry seen
- Very good energy resolution

Gas gains in Argon



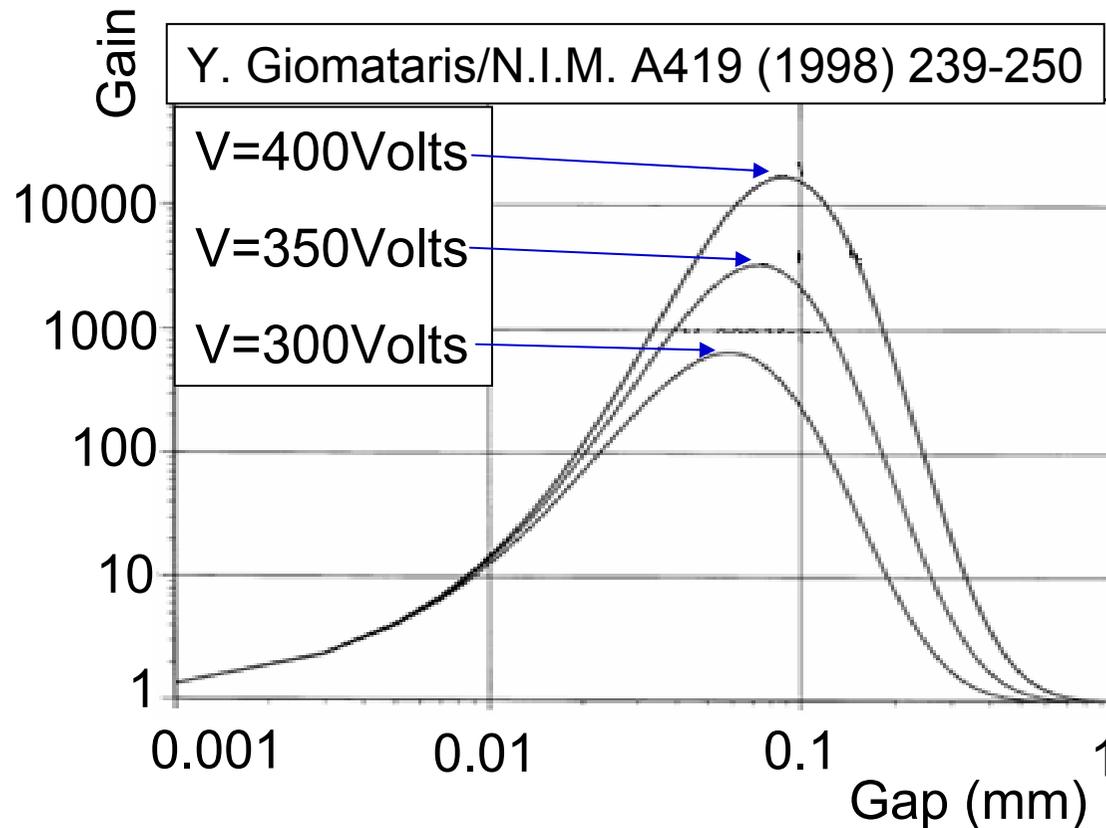
- Ar / CO_2 mixtures offer good ageing properties
- Gain of 10^4 reachable in Ar / CO_2 80/20
- Ageing studies in a reasonable amount of time (intense X-rays source)

Any field structure feasible



Gain for different gap sizes

Maximum predicted in gain vs gap curve



$$M = e^{\alpha d}$$

d gap thickness

$$\alpha = pAe^{-Bp/E}$$

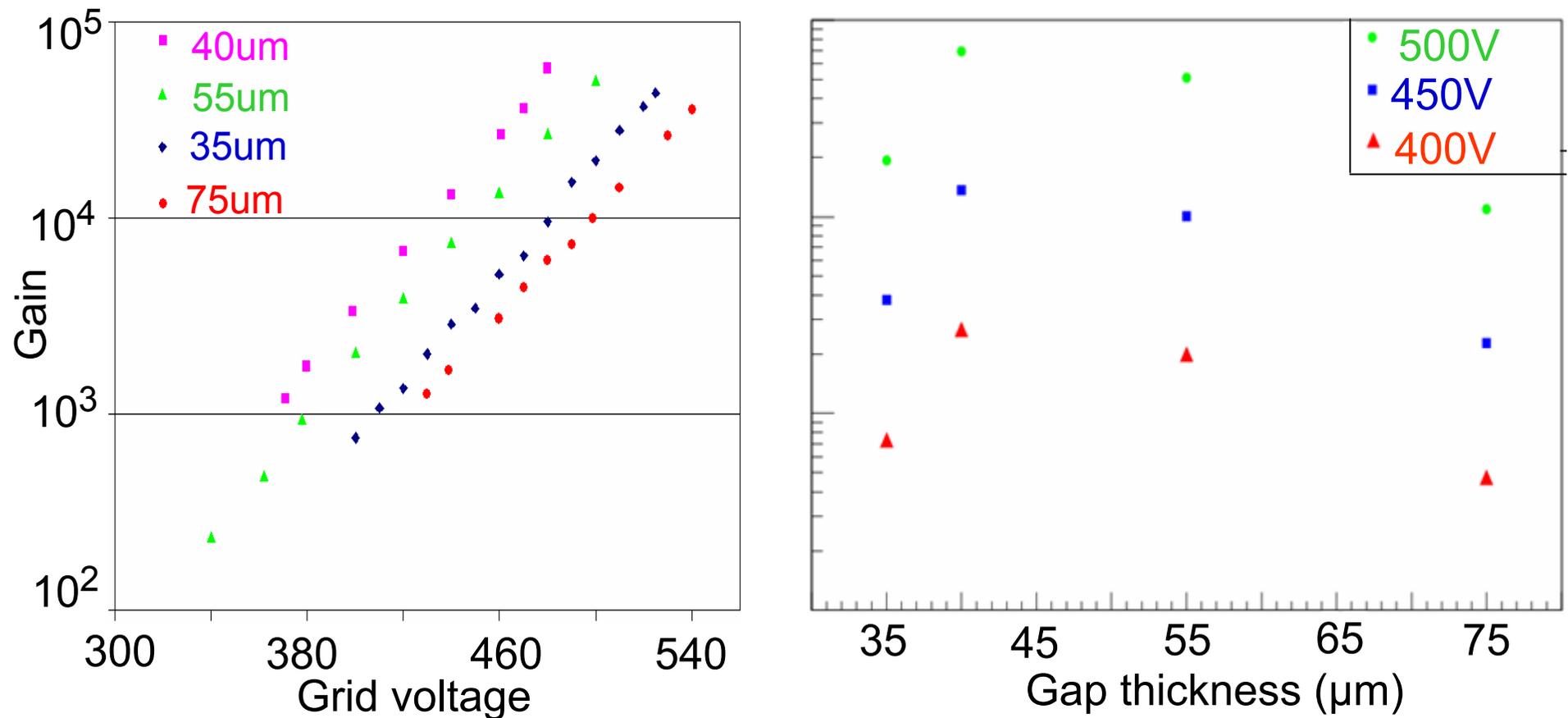
Rose & Korff

p pressure

A, B depend on gasmixture

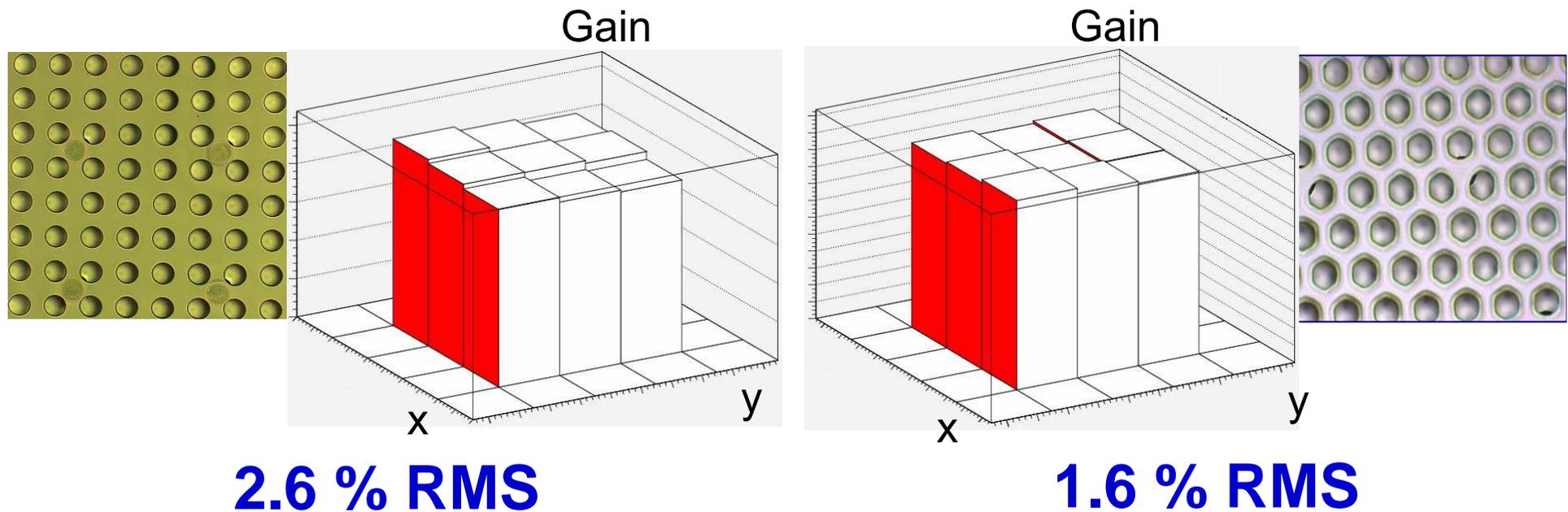
Gain for different gap sizes

- But now we can make measurements



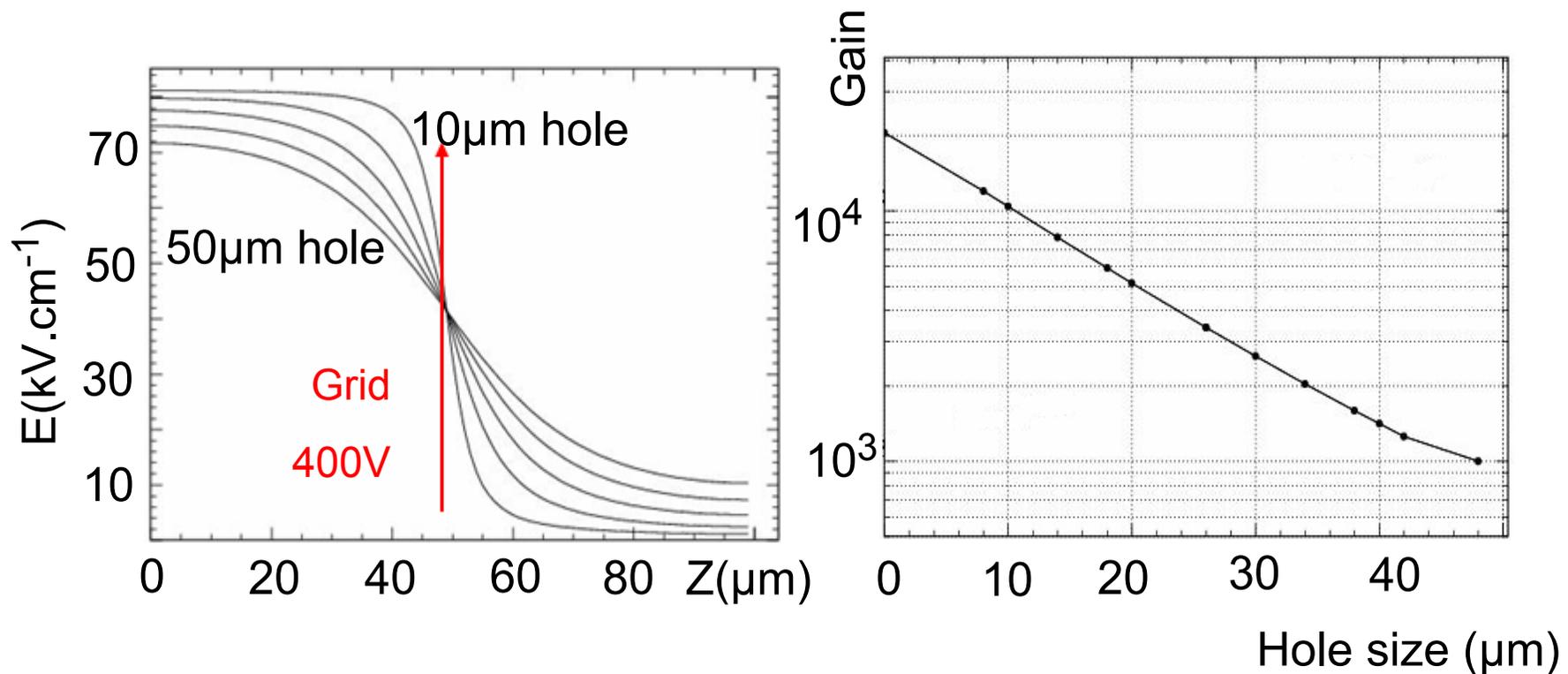
Homogeneity

- Gain measurements scanning the surface of the detector
- Homogeneity given by grid quality



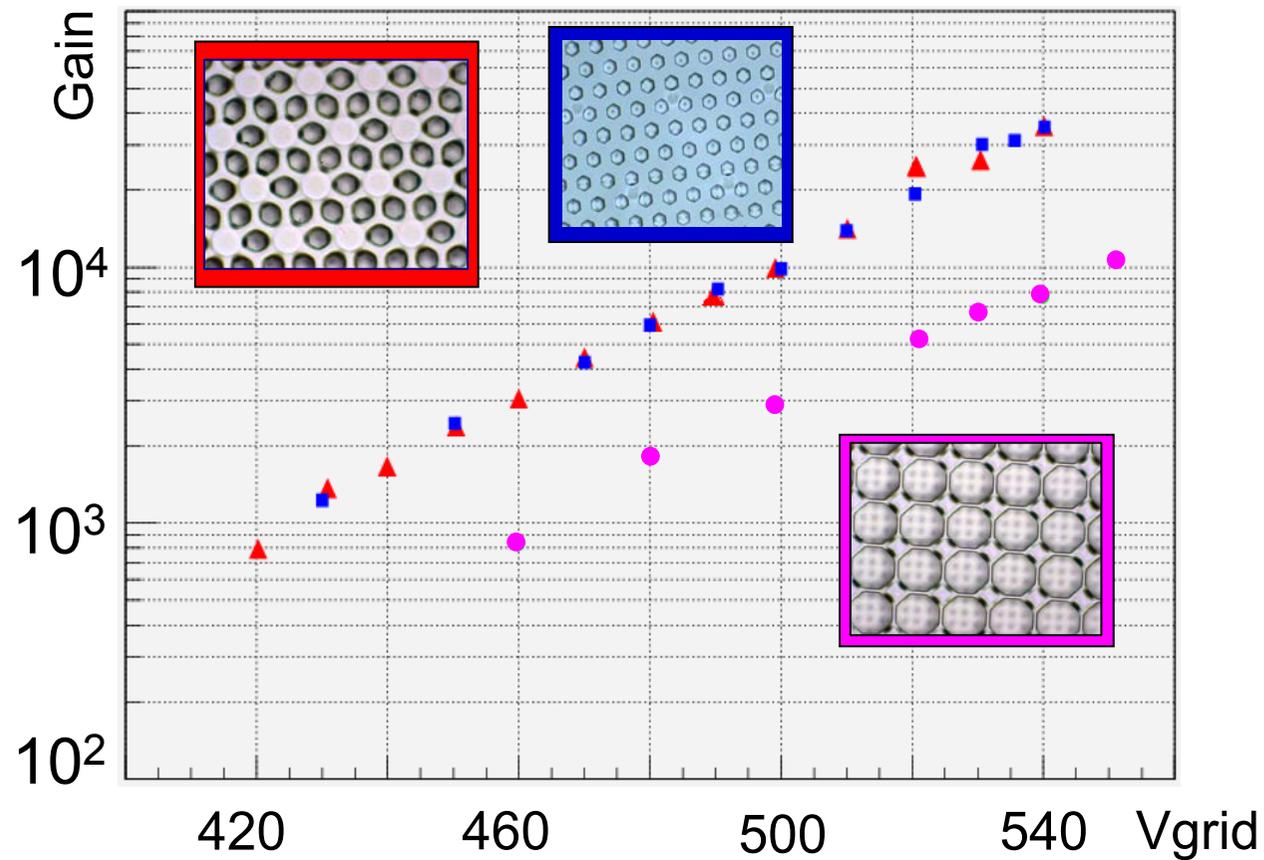
Simulated gain for different hole size

- Electric field along z axis decreases with hole size
- Different gain expected for different hole size



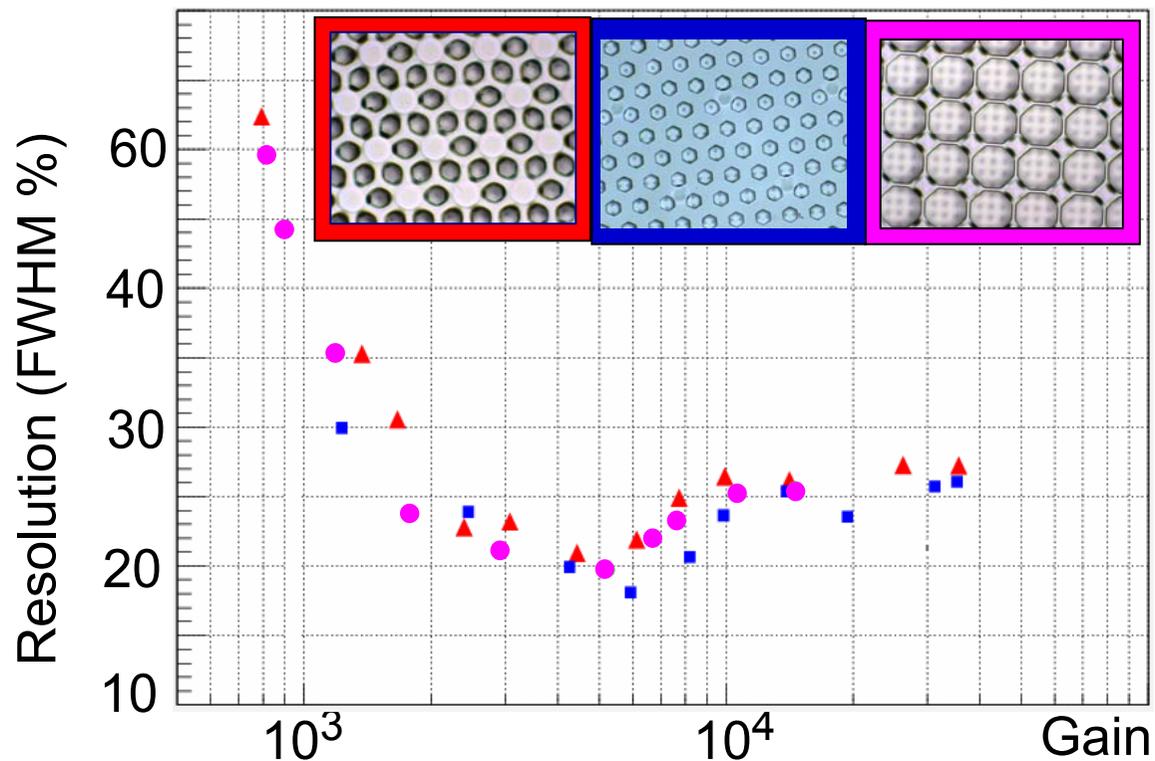
Measured gain for different hole size

And measurements confirm simulations



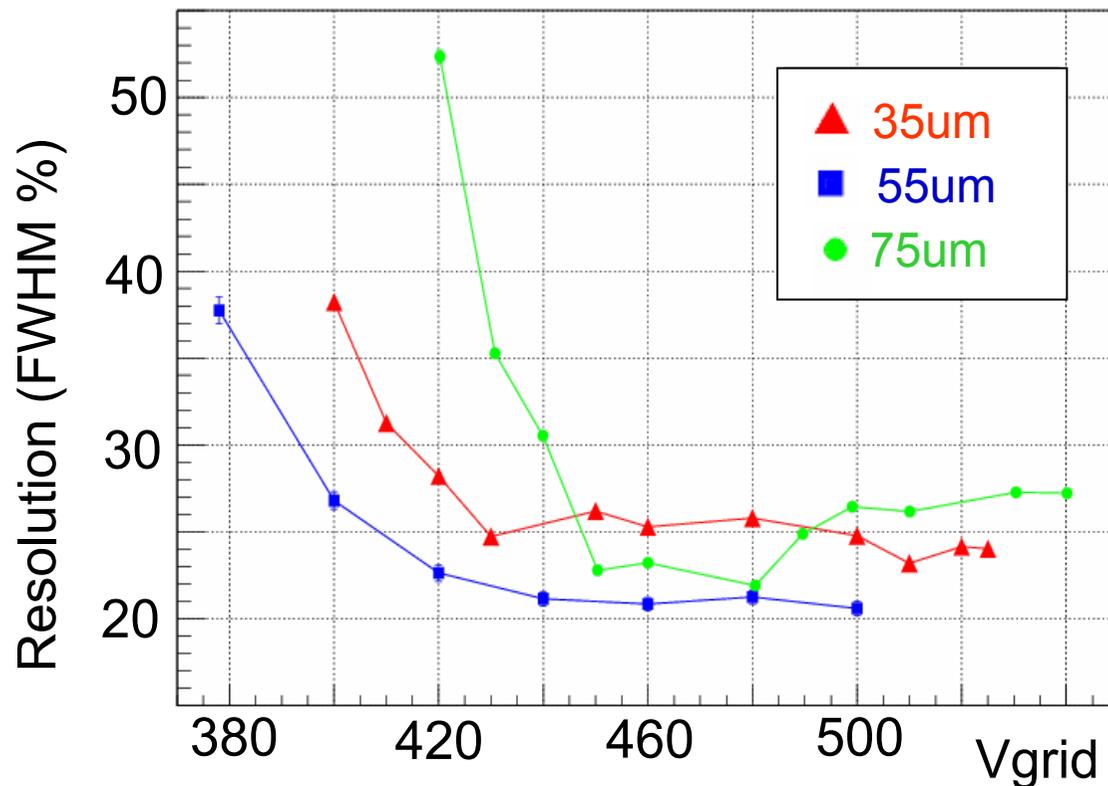
Energy resolution

- Resolution depends on
 - Primary, attachment, T,P
 - Collection efficiency (field ratio)
 - Gain homogeneity & transverse diffusion

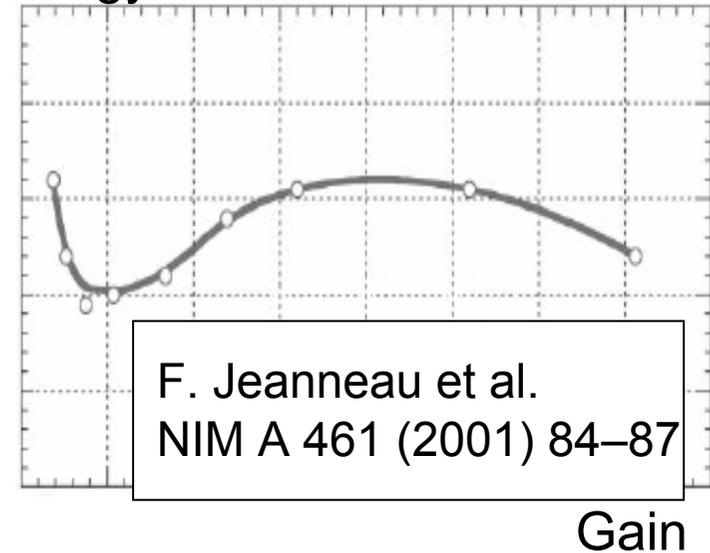


Resolution as function of gap

- Why a parabolic behavior ?

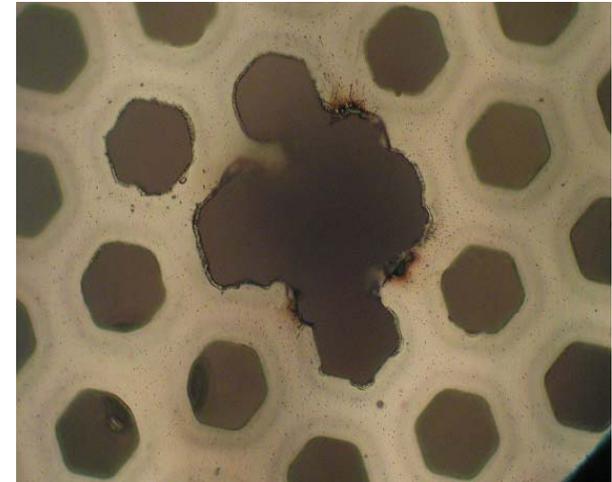
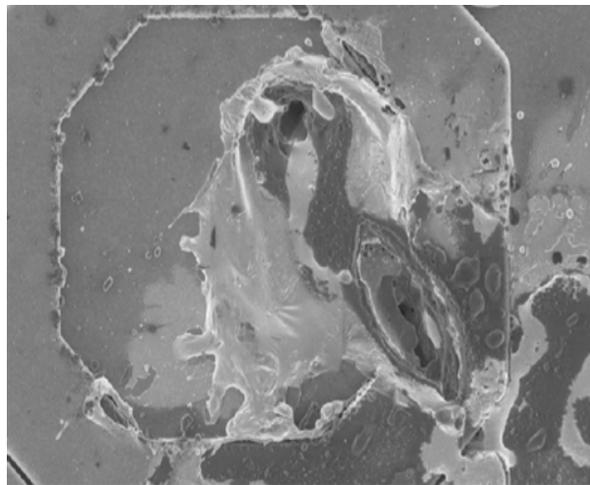
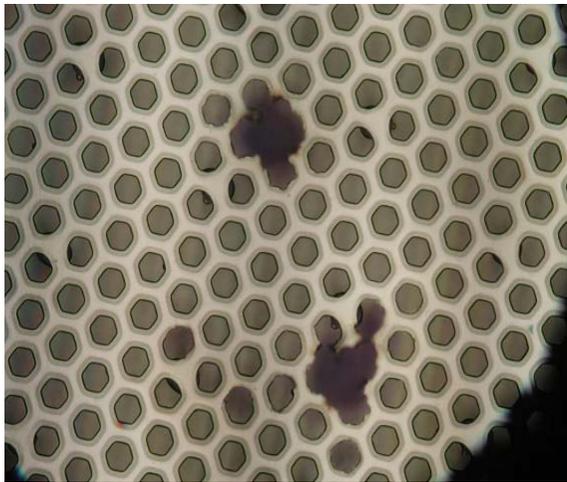


Energy resolution



Sparking

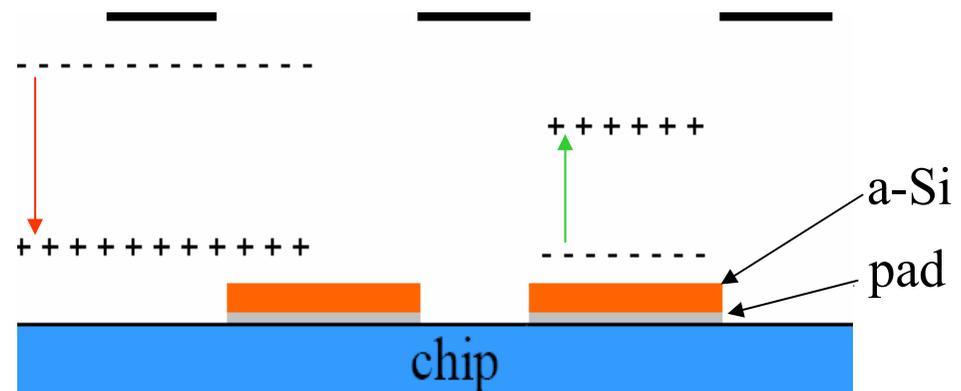
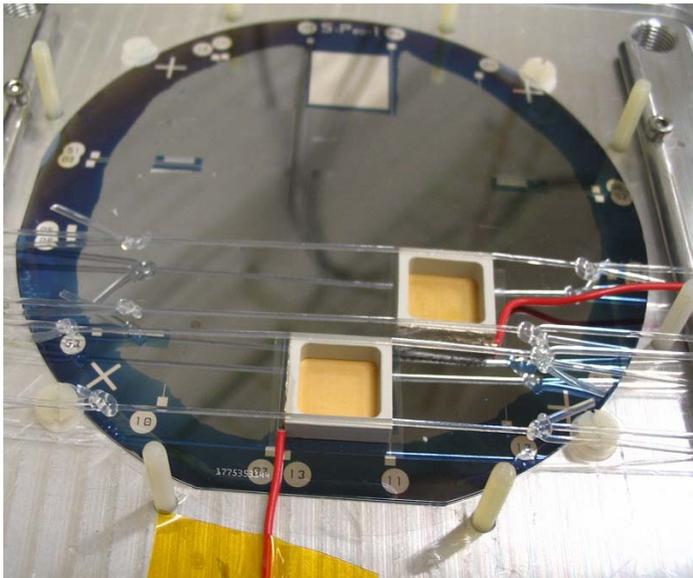
- Chip faces 80kV/cm with no protection (unlike the GEM setup)
- Degradation of the field, or total destruction of grid but also CMOS chip



10 μ m

Solution:high resistive layer

- Resistive plate chamber principle
- Amorphous silicon deposited
 - 4um thickness, resistivity $\sim 10^{11}\Omega\cdot\text{cm}$, temperature $\sim 250^\circ\text{C}$
- 2 fields with Micromegas: one protected, one unprotected
- First signals recorded; they look the same



SiProt

Protection of CMOS Pixel chip against discharges (sparks)

Method: apply high-resistive layer onto chip:

Principle: Resistive Plate Chamber

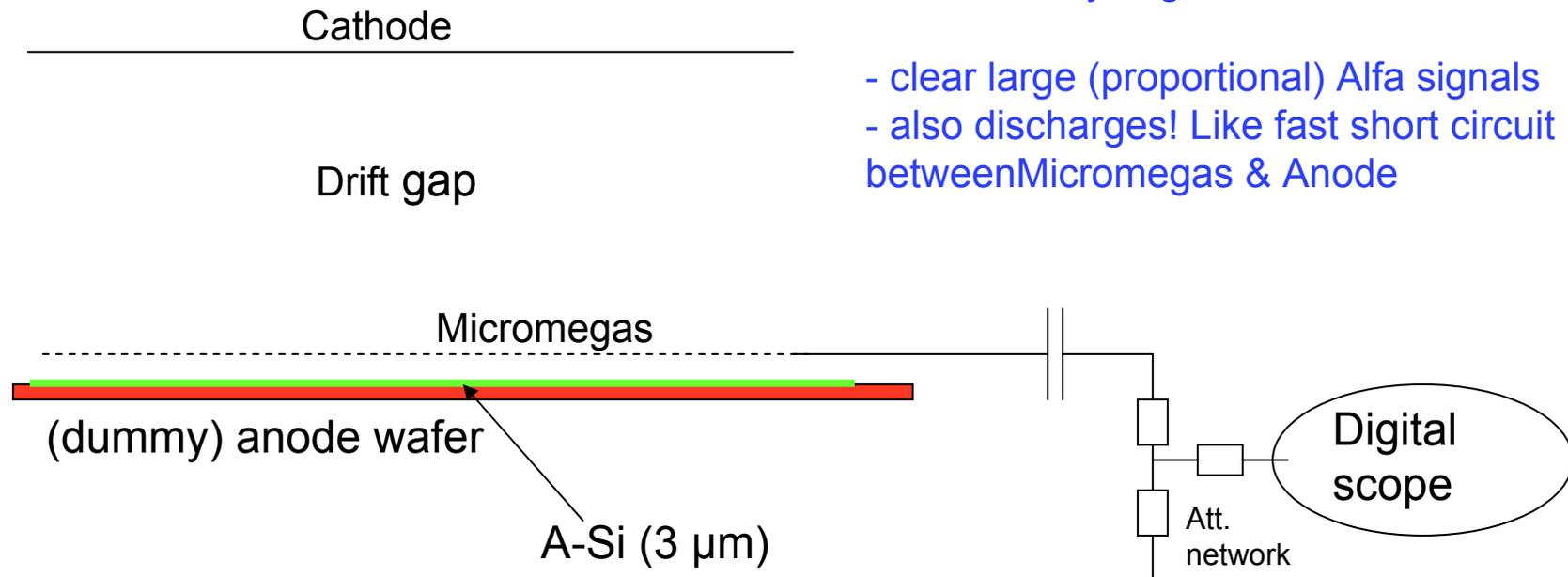
Univ. of Neuchatel (IMT): 3 μm of Amorphous Silicon without heating the Si wafer too much.....

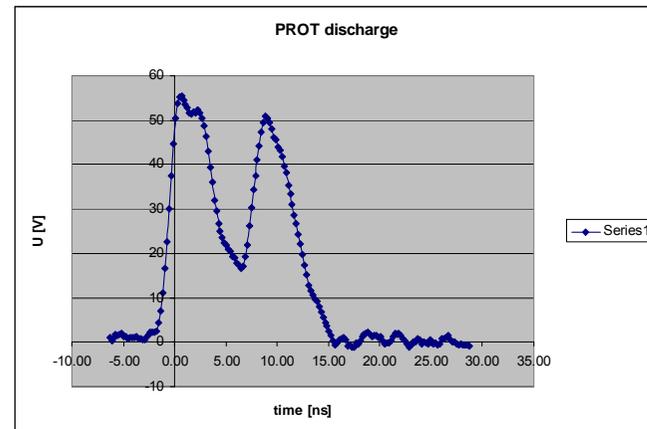
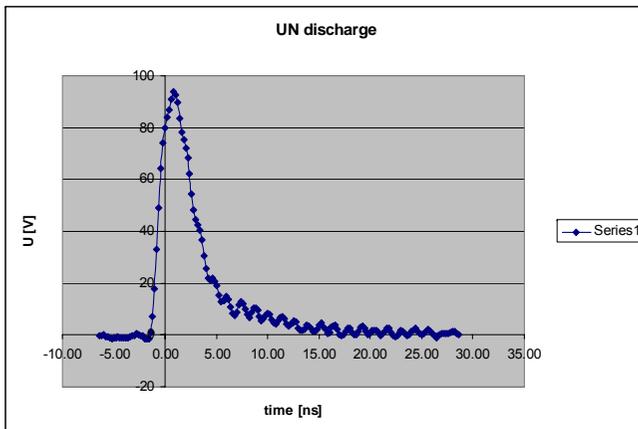
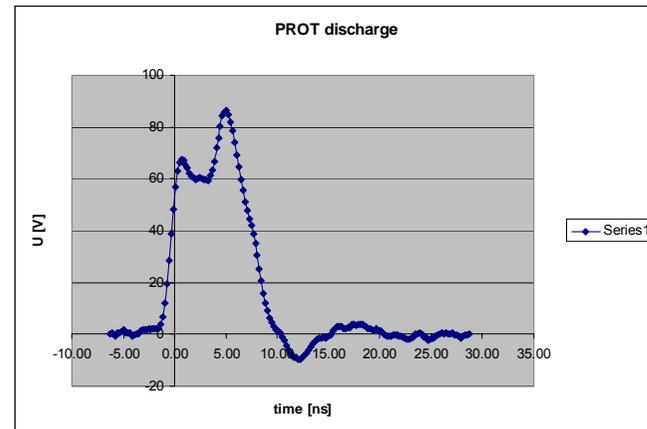
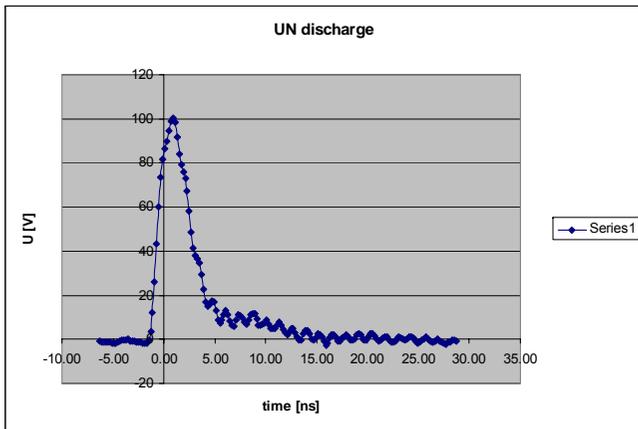
Put Thorium in gas line:

→ Radon gas

→ Alfa decay in gas

- clear large (proportional) Alfa signals
- also discharges! Like fast short circuit between Micromegas & Anode

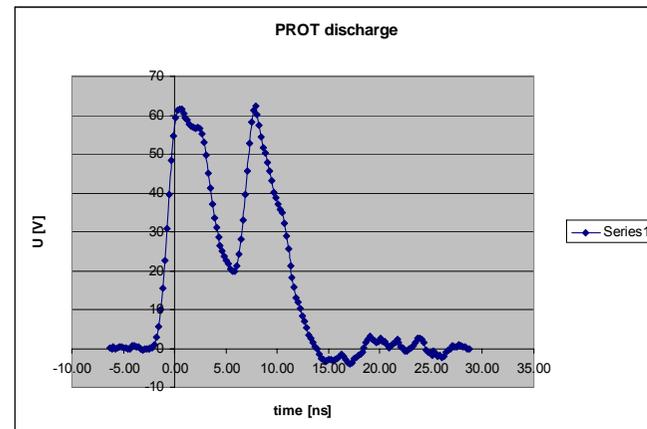




Unprotected: no A-Si layer

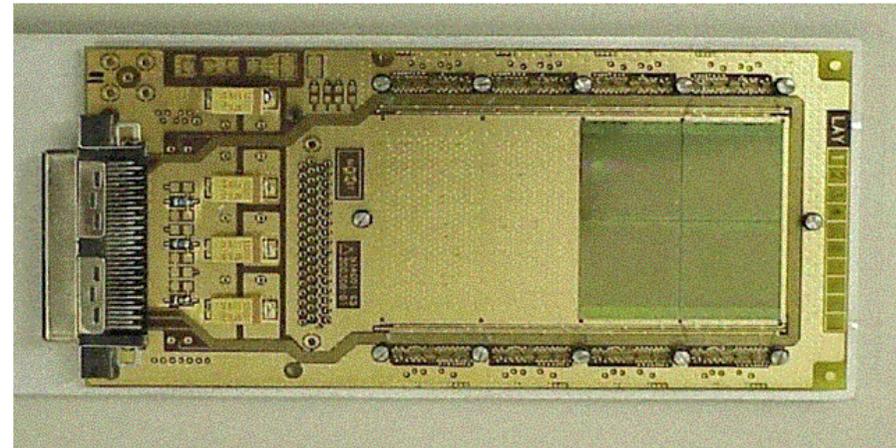
With protective A-Si layer

- smaller initial charge;
- 2nd discharge due to charge spread over surface?
- segmentation of A-Si layer in 'pixels'



Further Tests and Developments

- Investigate possible use of CMS (or Atlas) frontend pixel chip
- **GOSSIP**: very thin gas/pixel detectors as Vertex Detector (LHC/ILC) (TIMEPIX2 with ~ 1 ns resolution)
- Further ageing tests (Gossip)....
- **Chip tiling**: large(r) detector surfaces (2x2, 2x4 chips)
- **Through Si connectivity**: avoiding bonding wires
- **Fast readout technology**
(~ 5 Gb/s)
- **Discharge protection!**



NIKHEF

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Univ. Twente/Mesa+

Jurriaan Schmitz
Cora Salm
Victor Blanco Carballo
Sander Smits

CERN

Michael Campbell, Erik Heine
Xavi Llopart

GridPix: the electronic bubble chamber

